

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SD667, 2SD667A

Silicon NPN Epitaxial

RENESAS

ADE-208-1137 (Z)

1st. Edition

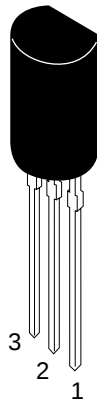
Mar. 2001

Application

- Low frequency power amplifier
- Complementary pair with 2SB647/A

Outline

TO-92MOD



1. Emitter
2. Collector
3. Base

2SD667, 2SD667A

Absolute Maximum Ratings (Ta = 25°C)

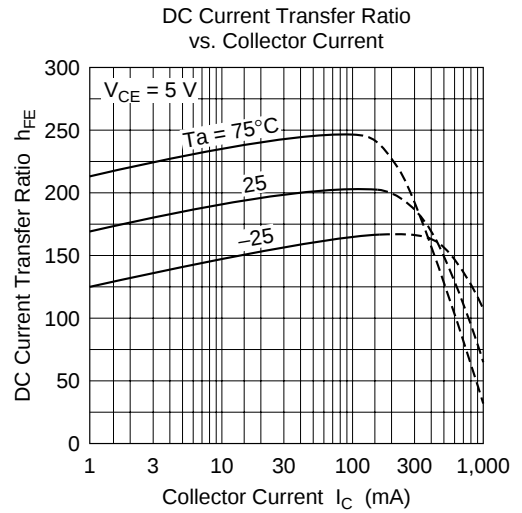
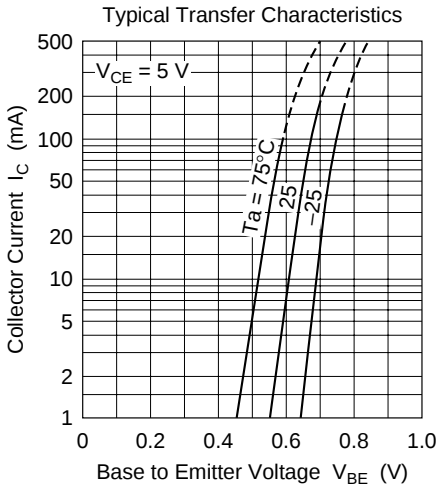
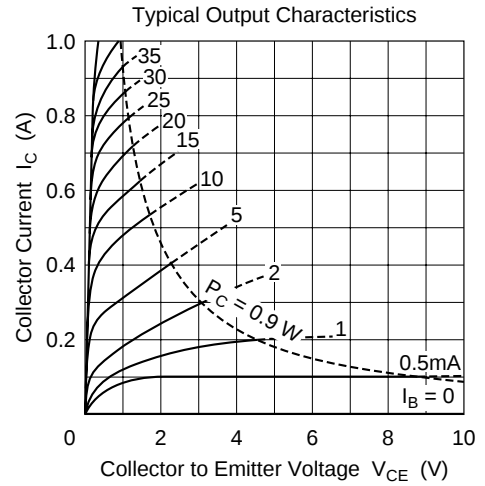
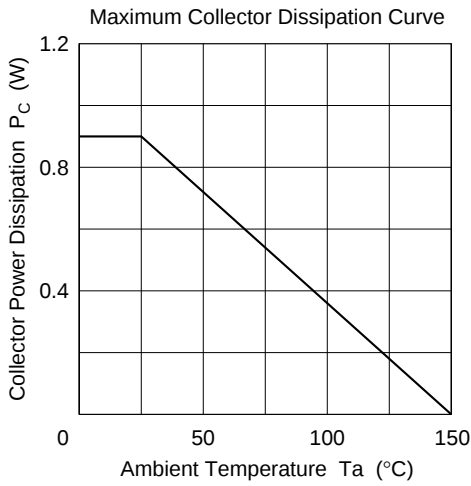
Item	Symbol	2SD667	2SD667A	Unit
Collector to base voltage	V _{CBO}	120	120	V
Collector to emitter voltage	V _{CEO}	80	100	V
Emitter to base voltage	V _{EBO}	5	5	V
Collector current	I _C	1	1	A
Collector peak current	i _{C(peak)}	2	2	A
Collector power dissipation	P _C	0.9	0.9	W
Junction temperature	T _j	150	150	°C
Storage temperature	T _{stg}	−55 to +150	−50 to +150	°C

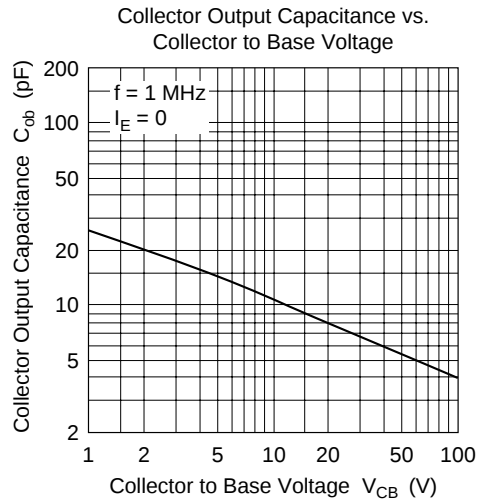
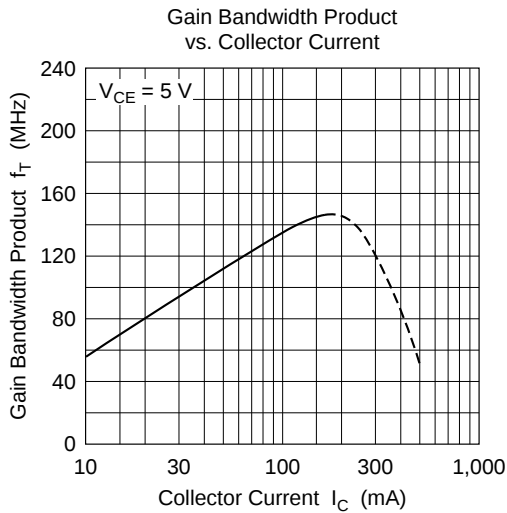
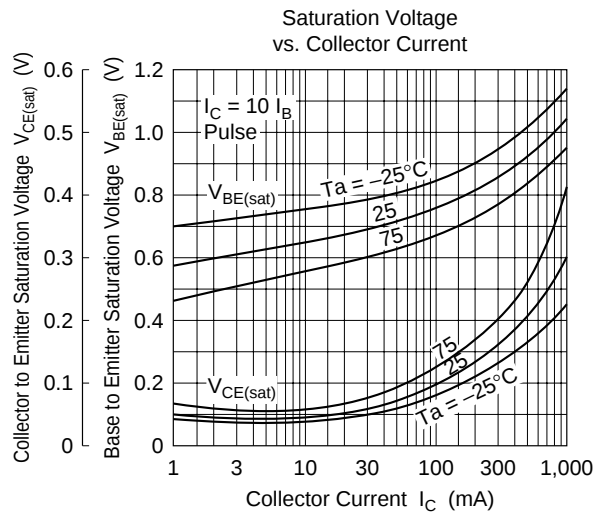
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SD667			2SD667A			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	V _{(BR)CBO}	120	—	—	120	—	—	V	I _C = 10 μA, I _E = 0
Collector to emitter breakdown voltage	V _{(BR)CEO}	80	—	—	100	—	—	V	I _C = 1 mA, R _{BE} = ∞
Emitter to base breakdown voltage	V _{(BR)EBO}	5	—	—	5	—	—	V	I _E = 10 μA, I _C = 0
Collector cutoff current	I _{CBO}	—	—	10	—	—	10	μA	V _{CB} = 100 V, I _E = 0
DC current transfer ratio	h _{FE1} ^{*1}	60	—	320	60	—	200		V _{CE} = 5 V, I _C = 150 mA ^{*2}
	h _{FE2}	30	—	—	30	—	—		V _{CE} = 5 V, I _C = 500 mA ^{*2}
Collector to emitter saturation voltage	V _{CE(sat)}	—	—	1	—	—	1	V	I _C = 500 mA, I _B = 50 mA ^{*2}
Base to emitter voltage	V _{BE}	—	—	1.5	—	—	1.5	V	V _{CE} = 5 V, I _C = 150 mA ^{*2}
Gain bandwidth product	f _T	—	140	—	—	140	—	MHz	V _{CE} = 5 V, I _C = 150 mA ^{*2}
Collector output capacitance	Cob	—	12	—	—	12	—	pF	V _{CB} = 10 V, I _E = 0, f = 1 MHz

Notes: 1. The 2SD667 and 2SD667A are grouped by h_{FE1} as follows.
2. Pulse test

	B	C	D
2SD667	60 to 120	100 to 200	160 to 320
2SD667A	60 to 120	100 to 200	

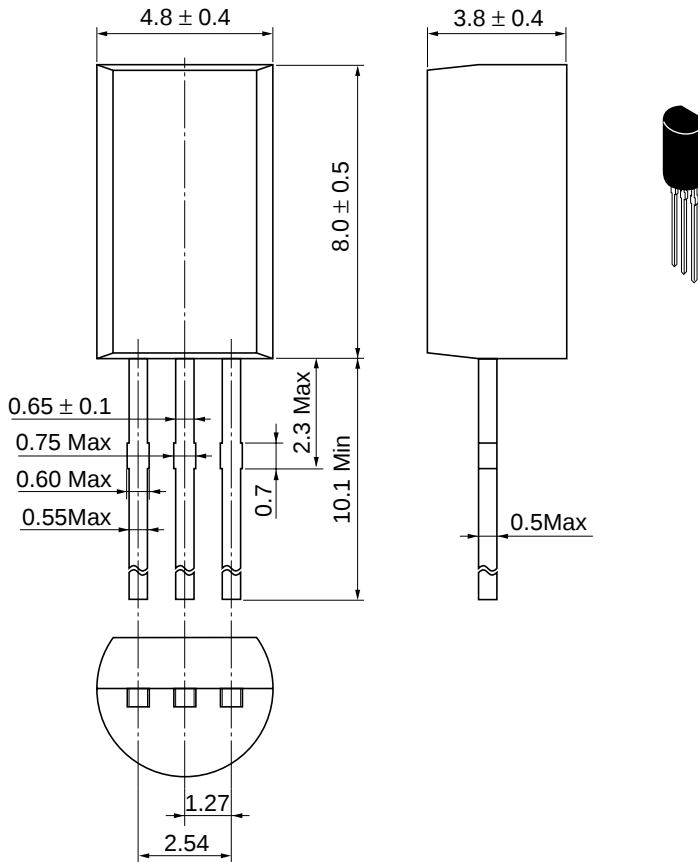




Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.35 g

Cautions

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	:	http://semiconductor.hitachi.com/
	Europe	:	http://www.hitachi-eu.com/hel/ecg
	Asia	:	http://sicapac.hitachi-asia.com
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For further information write to:

Hitachi Semiconductor
(America) Inc.

179 East Tasman Drive,
San Jose, CA 95134

Tel: <1> (408) 433-1990

Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group

Dornacher Straße 3
D-85622 Feldkirchen, Munich

Germany

Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.

Electronic Components Group.

Whitebrook Park

Lower Cookham Road

Maidenhead

Berkshire SL6 8YA, United Kingdom

Tel: <44> (1628) 585000

Fax: <44> (1628) 585160

Hitachi Asia Ltd.

Hitachi Tower

16 Collyer Quay #20-00,

Singapore 049318

Tel: <65>-538-6533/538-8577

Fax: <65>-538-6933/538-3877

URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.

(Taipei Branch Office)

4/F, No. 167, Tun Hwa North Road,

Hung-Kuo Building,

Taipei (105), Taiwan

Tel: <886>-(2)-2718-3666

Fax: <886>-(2)-2718-8180

Telex: 23222 HAS-TP

URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.

Group III (Electronic Components)

7/F., North Tower,

World Finance Centre,

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon,

Hong Kong

Tel: <852>-(2)-735-9218

Fax: <852>-(2)-730-0281

URL: <http://www.hitachi.com.hk>